MT6L56E

TOSHIBA

Preliminary

TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

MT6L56E

VHF-UHF Band Low Noise Amplifier Application VHF-UHF Band Oscillator Application

Two devices are built into the super-thin and ultra-super-mini (6-pin) ٠ ES6 package.

Mounted Devices

	Q1: SSM (TESM)	Q2: TESM
Three-pin (SSM/TESM) product No.	MT3S07S (MT3S07T)	MT3S08T

Maximum Ratings (Ta = 25°C)

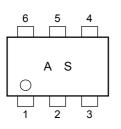
Characteristics	Symbol	Q1	Q2	Unit		
Collector-base voltage	V _{CBO}	10	20	V		
Collector-emitter voltage	V _{CEO}	5	8	V		
Emitter-base voltage	V _{EBO}	1.5	1.5	V		
Collector current	۱ _C	25	40	mA		
Base current	Ι _Β	7	10	mA		
Collector power dissipation	P _C (Note 1)	150		mW		
Junction temperature	Тј	125		125		°C
Storage temperature range	T _{stg}	-55~125		-55~125		°C

015±000
1.COLLECTOR1 4.BASE2
2.EMITTER1 5.EMITTER2
3.COLLECTOR2 6.BASE1
JEDEC —
JEITA —
TOSHIBA 2-2N1C

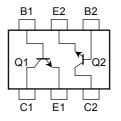
Weight: 3 mg (typ.)

Note 1: Total power dissipation of Q1 and Q2 mounted on the circuit board

Marking



Pin Connections



Electrical Characteristics Q1-Side (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 5 V$, $I_E = 0$	—	_	0.1	μA
Emitter cut-off current	I _{EBO}	$V_{EB} = 1 \text{ V}, \text{ I}_{C} = 0$		_	1	μA
DC current gain	h _{FE}	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$	70	_	140	_
Transition frequency	f _T	$V_{CE} = 3 V, I_{C} = 10 mA$	10	12	_	GHz
Insertion gain	S _{21e} ² (1)	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ f} = 2 \text{ GHz}$		6.5	_	dB
	S _{21e} ² (2)	$V_{CE} = 3 V$, $I_{C} = 15 mA$, f = 2 GHz	4	7	_	
Noise figure	NF (1)	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ f} = 2 \text{ GHz}$		1.6	3	dB
	NF (2)	$V_{CE} = 3 V, I_C = 5 mA, f = 2 GHz$	—	1.5	3	чв
Reverse transfer capacitance	C _{re}	$V_{CB} = 1 V, I_E = 0, f = 1 MHz$ (Not	te 2) —	0.45	0.85	pF

Electrical Characteristics Q2-Side (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0$	_		0.1	μA
Emitter cut-off current	I _{EBO}	$V_{EB} = 1 \text{ V}, \text{ I}_{C} = 0$	—	_	1	μA
DC current gain	h _{FE}	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$	80	_	140	—
Transition frequency	f _T	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$	2	4.5		GHz
Insertion gain	S _{21e} ² (1)	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ f} = 1 \text{ GHz}$	_	9.5		dB
	S _{21e} ² (2)	$V_{CE} = 3 \text{ V}, \text{ I}_{C} = 20 \text{ mA}, \text{ f} = 1 \text{ GHz}$	9.5	12.5		ub
Noise figure	NF	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ f} = 1 \text{ GHz}$	_	1.4	2.5	dB
Reverse transfer capacitance	C _{re}	$V_{CB}=1 \ V, \ I_{E}=0, \ f=1 \ MHz \qquad (Note$	2) —	0.55	0.95	pF

Note 2: C_{re} is measured by 3 terminal method with capacitance bridge.

Handling Precaution

When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

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